Atomic structure of carbon centres in hBN: towards engineering of single photon sources

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Revealing atomic and electronic structure of quantum defects in carbon doped hexagonal boron nitride (hBN:C) is crucial for the development of future technology to integrate them within solid state devices. Here, we investigate atomically thin hBN:C films deposited on graphite substrates via scanning tunnelling microscopy and spectroscopy. We observe positively charged defect centres which lower the onset of differential conductance below the conduction band of the host material and induce narrow resonances in the mid-gap regime of the tunnelling spectra. We corroborate atomically-resolved lattice structure of defect sites and their mid-gap states observed in tunnelling dI/dV spectra with the predictions of the atomic and electronic structure of carbon impurities in hexagonal boron nitride by density functional theory. Our findings demonstrate that carbon substitution for boron constitutes a stable and energetically favourable impurity. Its unique properties, when analysed comparatively with other plausible defect centres, provide a good agreement with our experimental observations.

Defect centres in crystals can transform the characteristics of host materials by modulating their fundamental electronic properties or even raising novel phenomena. Recently, optical inspection of hexagonal boron nitride (hBN) unveiled a variety of luminescent centres that act as single photon sources in extraordinarily broad spectral range1-4. The wide band gap character of hBN5,6 enables formation of emitters that are optically active in ultraviolet, visible and infrared region. Moreover, these luminescent centres appear to be particularly resilient by displaying stable photoluminescence (PL) and single photon emission in ambient conditions7, despite being unprotected from environment in atomically thin hBN films.

Currently, the pending identification of specific defects in hBN constitutes a fundamental limitation in understanding the electronic structure of the emergent luminescent centres. Resolving this issue can establish novel atomically precise systems based on doped hBN that provide functionalities in the domain of spin manipulation, quantum sensors and light sources akin to modern utilities of well-known defect centres in 3D lattices. Moreover, creation and characterisation of specific defects in atomically thin films, down to individual monolayers, is likely to enable a range of new applications. These may include efficient coupling of the emissive centres to photonic structures, fabrication of strongly planarized single-spin devices or electrically driven on-demand single photon sources.
Figure 1. Optical characterisation of exfoliated hBN:C films. (a) The μPL spectra were measured for several flakes under 514 nm (2.41 eV) excitation conditions at low temperature. Multiple resonances form a reproducible spectral pattern with additional lines appearing at specific spots within the hBN:C films. (b) The optical images of the flakes confronted with PL mapping experiments, when (c) the PL intensity is monitored at the energy of particular lines, demonstrate homogenous optical response and (d) enables identification of spots with localised emitters.

In order to progress towards these exciting functionalities, we identify defect centres in carbon-doped few-layers hBN films via scanning tunnelling microscopy probes. By displaying homogenous and reproducible optical response, these films became perfect candidates for the inspection of the nature of the emergent defects in atomic scale. In this work, we utilize the two-dimensional (2D) crystal structure of hBN, to create heterostructures enabling characterisation of defect centres by scanning tunnelling microscopy (STM) and scanning tunnelling spectroscopy (STS). Particularly, we inspect thin layers of carbon doped hBN (hBN:C), unveiling the presence of a specific defect centre: a carbon substitution for boron (C$_0$). We explore its atomic and electronic structure by the tunnelling probes and corroborate our findings with density functional theory (DFT) predations of the properties of single-particle mid gap states arising due to such carbon impurity.

The hBN crystals used for this study were grown by the temperature gradient method in high-pressure and high-temperature conditions. The carbon doping of hBN was induced by annealing the pristine hBN specimens in a graphite furnace for 1 h at 2000 °C. The inspection of low temperature (1.6 K) PL spectra of exfoliated hBN:C films demonstrate a spatially homogenous optical response as illustrated in Fig. 1. A specific pattern of optical resonances arises within a spectral region of 1 eV width in visible and near infrared range. The reproducible multi-line pattern seen in the PL spectra is enriched by additional resonances at specific spots of the hBN:C films which can be identified by PL mapping experiments (Fig. 1(c,d)). Overall, the complex optical response of the hBN:C films is unlikely to arise exclusively due to a single type of a defect centre hence further characterisation methods are needed to unveil their atomic and electronic structure. In order to enable STM inspection of highly

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A The energy region of observable PL resonances is limited by the detection range of a silicon charge coupled device camera (at low energy side) and by the laser excitation conditions (at high energy side).
resistive hBN crystals, we fabricated heterostructures that are composed of 3 atomic layers (3L) of hBN:C deposited onto conductive graphite layers that allows probing of the hBN:C lattice via local tunnelling of charge carries. The use of several layers of hBN:C allows for the top layer to be sufficiently decoupled from graphite, whereas still allowing investigation of STM. A schematic representation of our experiment is shown in Fig. 2a. The initial low temperature (T = 4.7 K) STM characterisation of our samples reveals emergence of a moiré superlattice within the region of the heterostructure\textsuperscript{14,20-26}. Based on the STM image presented in Fig. 2b, we establish the periodicity of the moiré pattern to be 4.16 ± 0.01 nm, which corresponds to a twist angle of θ=3.3° between the graphite and hBN:C hexagonal lattices. Independently, STM image of hBN:C acquired over the surface region free of defects/impurities resolves the lattice constant of 0.25 ± 0.01 nm, consistent with that of pristine hBN\textsuperscript{27}.

Figure 2. STM characterisation of a van der Waals hBN:C/graphite heterostructure. (a) A schematic illustration shows our experimental configuration. The graphite substrate is grounded via a golden electrode while the sample bias (V\textsubscript{S}) is applied to the STM tip. (b) Atomically-resolved STM image of hBN:C layers reveals emergence of a moiré superlattice in the region of interest (V\textsubscript{S} = 3.2 V, I\textsubscript{I} = 10 pA, T = 4.7 K). We utilise the appearance of the moiré pattern as an indicator that we probe the tunnelling processes within the area of the hBN:C/graphite heterostructure.

Multiple defect centres manifest themselves in large-scale STM images via modulation of the density of states available for the tunnelling processes (Fig. 3a). The best contrast for visualisation of these defect sites is achieved at relatively high positive sample bias V\textsubscript{S}, at which individual defect site exhibits a circular protrusion. A statistical analysis of multiple STM images reveals a defect density of 2.4\times10\textsuperscript{10} cm\textsuperscript{-2} per atomic layer in our hBN:C material (under the assumption of a homogeneous distributions of the defect sites across the entire heterostructure). It is also noted that defect centres show three representative apparent heights in the constant-current STM images (Fig. 52), suggesting that these defects are located in three different layers of hBN:C flakes. The majority of defect sites display bright contrast at positive sample bias and dark halo at negative sample bias, as illustrated in Fig. 3b and 3c respectively. This bias-dependent STM contrast signifies that defect centres are positively charged, creating a local electrostatic field that facilities (suppresses) electron (hole) tunneling into empty states (occupied states), respectively\textsuperscript{28,29}. The atomic-resolution STM image taken at V\textsubscript{S} = −3 V (Fig. 3d) reveals intact atomic lattice expected for hBN:C but with a slight modification of lattice contrast, suggesting that these defects are likely created by the substitution of N or B atoms with carbon atoms.
Figure 3. Real-space STM imaging of defect centres. The STM experiment allows for the visualisation of atomic structures of defects within individual atomic layers of hBN:C. (a) Large-scale STM image reveals the presence of multiple defect centres ($V_s = 6.8$ V, $I_t = 10$ pA). The majority of the defect centres exhibit (b) bright protrusion acquired at positive sample biases ($V_s = 4.5$ V, $I_t = 100$ pA) and (c) dark halo acquired at negative sample biases ($V_s = -5$ V, $I_t = 100$ pA). (d) Lattice-resolved STM image reveals the atomic structure of individual defect centres ($V_s = -3$ V, $I_t = 50$ pA). Scale bar is 2 nm in panel (b-d).

For further identification of the emergent defect types, we performed spatially resolved $dI/dV$ spectroscopic measurement over a pristine hBN lattice site and this dominant defect site\(^8\). Within the region of perfect hBN crystal structure, the onsets of the differential conductance correspond to the edges of the valence and conduction bands for the negative and positive sample biases, respectively. The band edges are better determined by further conducting the logarithm of $dI/dV$ curve shown in Figure 4a, whereby the band gap of 3L hBN film deposited on a graphite substrate is determined to be 6.20 ± 0.29 eV (refer to Fig. S4 in S. l. appendix\(^30\)). In contrast to perfect hBN region, $dI/dV$ spectrum taken over this dominant defect in hBN reveals prominent mid-gap states spanning over a bias range of 1.5 V < $V_s$ < 3.25 V. Multiple narrow resonances appear which form a band of about 1.5 eV width below the conduction band. We interpret the appearance of the mid-gap states as evidence of charge tunnelling processes via vacant defect-induced level(s). The broadband character of the subconduction band states indicates the existence of tunnelling processes with simultaneous emission of phonons\(^31\) into the hBN lattice, forming repetitive replicas of the electronic states in $dI/dV$ curves. The comparison between the $dI/dV$ resonances with the phonon density of states for the hBN lattice is presented in Fig. S6.

There are two possible types of defects that can introduce donor states below the conduction band without creating acceptor states above the valence band: (1) nitrogen vacancy ($V_N$) and (2) carbon substitution for boron ($C_B$). As both types of defects could give rise to the tunnelling characteristics observed in $dI/dV$ spectra, we performed additional analysis of the defect stability and electronic structure by DFT. Firstly, we compared the formation energy of single site and double site defects in carbon doped hBN crystal as presented in Fig. 5a. We found that among single site defects, $V_N$ is characterised by the largest and $C_B$ by that lowest formation energy. Moreover, our optical characterisation of carbon doped specimen reveals activation of optical response that follows Franck-

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\(^8\) The inspected defect sites were randomly selected from the group of defects identified in the large scale mapping experiment that show positive/negative contrast at positive/negative sample bias. We found that the presence of the donor level below the conduction band is a common observation for these types of defect. The lattice imperfections with the opposite contrast display unstable $dI/dV$ characteristics.
Condon principle with a significant electron-phonon coupling strength\textsuperscript{8,9}. The emergence of multiple phonon replicas, creating phonon sidebands that dominate over zero-phonon line in the optical spectra, is consistent with the multiline band observable in $dI/dV$ spectra taken at the defect sites. Therefore, we conclude that $C_6$ is a common defect centre in carbon doped hBN samples that is likely to give rise to mid-gap photoluminescence.

\begin{figure}[h]
\centering
\includegraphics[width=\textwidth]{figure4}
\caption{Mid-gap states introduced by the defect. (a) $dI/dV$ curves taken over a pristine hBN lattice and (b) over a defect site. The impact of the defect site is readily seen in the tunnelling spectra as a shift of the onset of $dI/dV$ signal on the positive bias side combined with an emergence of a narrow resonance. (c) A small-scale $dI/dV$ STS curve over a defect site for $1.5 \, V < V_S < 3.25 \, V$.}
\end{figure}

From the point of view of electronic structure\textsuperscript{32-35} of $C_6$ defect, carbon introduces one additional valence electron at the lattice site of boron, which gives rise to a half-filled mid-gap level below the conduction band. The orbital composition of the defect-induced level originates mostly from the $p_z$ orbital of the C atom. If the energy position of such level is higher than the Fermi level in graphite – the extra electron will tunnel to graphite substrate, leaving the defect positively charged\textsuperscript{36}, consistent with our STM observation.

In conclusion, scanning probe techniques allowed us to identify $C_6$ as a defect centre observable in carbon doped hBN crystals. We explored the atomic and electronic structure of this defect via STM and STS characterisation in combination with an analysis of its properties based on DFT theory. Our findings provide insights into the formation of a stable carbon-substituted defect centre in favour of other possible carbon-based impurities. The 2D character of hBN allows isolation of atomically thin films that host stable defect, which creates an opportunity to integrate them within solid state and/or flexible membrane-type devices. It is plausible, that with the increasing understanding of the atomic structure of defects in hBN, they may become realistic counterparts for other useful defect centres in wide gap materials, such as nitrogen-vacancy centres in diamond.
Methods

Sample fabrication. Graphite and hBN:C crystals were mechanically cleaved onto silicon wafers with 300 nm and 90 nm layers of SiO₂, respectively. Large-area graphite films were selected to act as conductive substrates for atomically thin hBN:C films (3 layers). The hBN:C flakes were transferred onto the graphite substrate via a pickup technique. The hBN:C flakes of desired thickness were identified by their optical contrast and atomic force microscopy. They were lifted from the Si/SiO₂ wafer with a polydimethylsiloxane/polycarbonate stamp at 100 °C. Subsequently, the hBN:C flakes were released onto the graphite film together with the polycarbonate film at 180°C, which renders a high-quality interface between the two materials. The sample was then annealed at 180°C on a hot plate and washed in dichloromethane, acetone and isopropanol to remove the polymer residues. Prior to the STM measurements, the sample was annealed in situ in ultra-high vacuum at 310°C for 12 h to remove surface residues and adsorbates.

Optical characterisation. The photoluminescence (PL) spectra were measured in microscopic (1 μm spot size) back-scattering geometry with 514 nm laser excitation. The sample was cooled down to 1.6 K through helium exchange gas. The sample was mounted on x-y-z piezo positioners that allowed PL mapping experiment. The PL signal from the sample was collected by a multimode fiber with 50 μm core diameter, dispersed by a 0.75 m spectrometer with 300 g/mm grating and detected by liquid-nitrogen-cooled charge coupled device camera.

Figure 5. The density functional theory predicts the formation energy and electronic structure of various types of single site and double site defect centres in carbon doped hBN lattices. (a) The values of the formation energy are presented for boron vacancy (V_B), nitrogen vacancy (V_N), carbon substitution for boron (C_B), carbon substitution for nitrogen (C_N) and their combinations C_BC_N, C_NV_B and C_BV_N. (b) The electronic structure of C_B opens tunnelling pathways that are consistent with the tunnelling dI/dV spectra observable for defect sites in carbon doped hBN films. (c) Schematic illustration of the atomic structure of single site and double site defect centres in hBN:C.
STM and STS measurements. Our STM and STS measurements were conducted at 4.7 K in the Createc LT-STM system with a base pressure lower than $10^{-10}$ mbar. Tungsten tip was calibrated spectroscopically against the surface state of Au(111) substrate. All the $dI/dV$ spectra were measured through a standard lock-in technique with a modulated voltage of 3-10 mV at the frequency of 700-900 Hz.

DFT calculations. The DFT calculations were performed using a generalized gradient approximation (GGA) to the exchange correlation functional proposed by Pedew, Burke and Ernzerhof (PBE) 37. All calculations were spin-polarized and used the projector augmented wave (PAW) pseudo-potential supplied with the VASP code38,39. A plane wave cut-off of 500 eV was used. Pristine single layer hBN was first optimized for the lattice geometry using the conventional cell and a 21x21x1 Monkhorst-Pack reciprocal space grid with an energy tolerance of 0.01 eV. A vacuum spacing of 20 Å was used to separate periodic images of the single layer and the lattice vectors in a conjugate gradient approach. A 5x5x1 supercell was used for the calculations of the defect properties in hBN. The structures were fully optimized using the conjugate gradient algorithm until the residual atomic forces were smaller than 10 meV/Å. A Γ-centered 12x12 k-point sampling was used for the Brillouin-zone integration. The method for the calculation of the formation energy of different defects existing in various charge states at the N-rich condition was the same as in the Ref.32.

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